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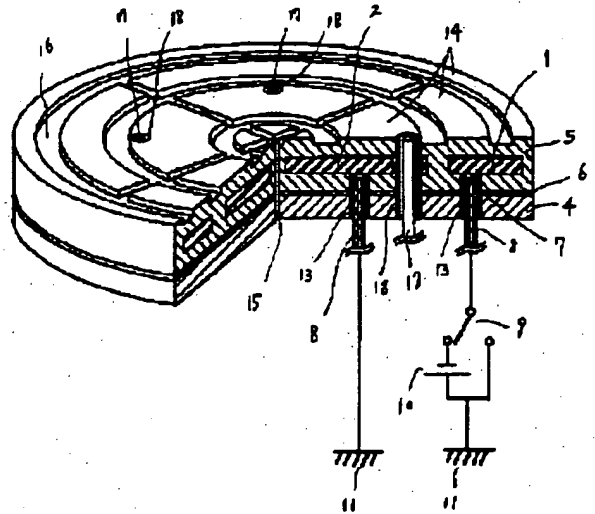
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APPLICANT : HITACHI LTD;

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TITLE : ELECTROSTATIC ATTRACTION
DEVICE



ABSTRACT : PROBLEM TO BE SOLVED: To efficiently generate an attraction force and to improve reliability by making the distance among a plurality of electrodes larger than the thickness of a dielectric film.

SOLUTION: In an electrostatic attraction device, a dielectric film 5 that is a sintered body of aluminum oxide where two electrodes, namely a ring electrode 1 and an inner electrode 2, are embedded concentrically inside on an aluminum block 4 is fixed by an adhesive 6. The overall dielectric film 5 is as thick as 1 mm and is machined, so that the thickness of the dielectric film on the two electrode embedded inside reaches 300 micron. Then, the ring electrode 1 and the inner electrode 2 are arranged with an interval sufficiently larger than the thickness of the dielectric film 5 on the electrode, namely 5 mm, and the resistance between the ring electrode 1 and the electrode 2 is set so that it is fully larger than the resistance between the wafer and the electrode. Consequently a leakage current that flows between electrodes is reduced since the resistance between the electrodes is larger than that between the electrode and an object to be attracted and fully achieving an attraction force by fully applying voltage between the electrode and the wafer is achieved fully.

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